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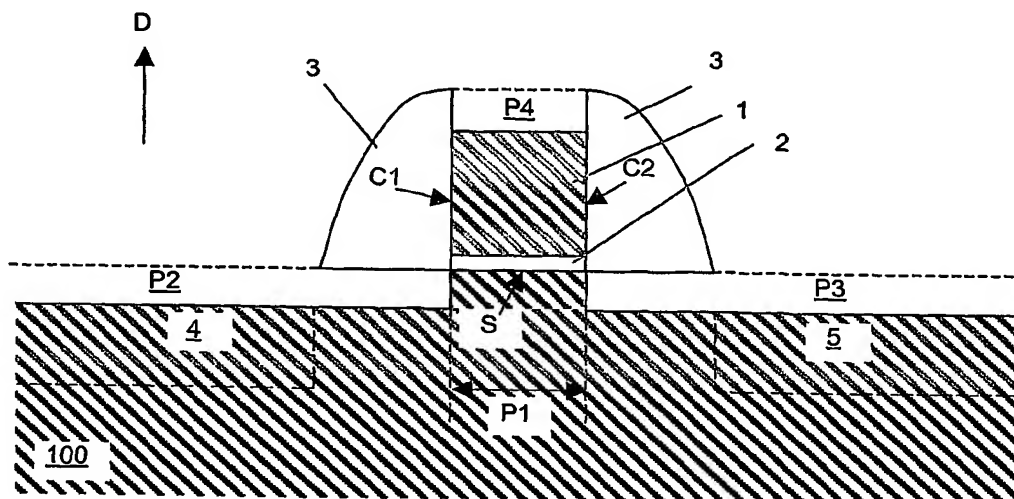
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(54) Title: SEMICONDUCTOR DEVICE COMPRISING EXTENSIONS PRODUCED FROM MATERIAL WITH A LOW MELTING POINT



(S7) Abstract: A semiconductor device comprises a gate electrode (1) and a gate insulating layer (2) both surrounded by a spacer (3) and produced on a surface (S) of a substrate (100) of a first semiconductor material. The device also comprises a source region (4) and a drain region (5) both situated below the surface of the substrate, respectively on two opposite sides of the gate electrode (1). The source region and the drain region each comprise a portion of a second semiconductor material (6, 7) disposed on the substrate (100) and extending between the substrate (100) and the spacer (3). The second material has a melting point lower than the melting point of the first material. The portions of second material (6, 7) constitute extensions of the source (4) and drain (5) regions. The semiconductor device can be an MOS transistor.

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